

## Features

- Trench Power LV MOSFET Technology
- Excellent Package for Heat Dissipation
- High Density Cell Design for Low  $R_{DS(ON)}$
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)
- Moisture Sensitivity Level 1

## Maximum Ratings

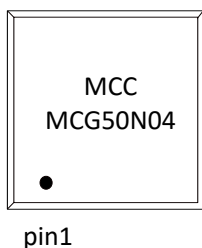
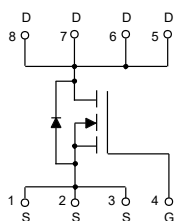
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 40°C/W Junction to Ambient<sup>(2)</sup>
- Thermal Resistance: 1.67°C/W Junction to Case<sup>(2)</sup>

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	40	V
Gate-Source Voltage	$V_{GS}$	±20	V
Continuous Drain Current	$I_D$	50	A
Pulsed Drain Current <sup>(3)</sup>	$I_{DM}$	200	A
Total Power Dissipation	$P_D$	75	W
Single Pulsed Avalanche Energy <sup>(4)</sup>	$E_{AS}$	400	mJ

Note:

1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design, while  $R_{\theta JA}$  is determined by the board design. The maximum rating presented here is based on mounting on a 1 in<sup>2</sup> pad of 2oz copper.
3. Pulse Test: Pulse Width ≤ 300us, Duty cycle ≤ 2%.
4.  $T_J = 25^\circ\text{C}$ ,  $V_{DD} = 30\text{V}$ ,  $V_{GS} = 10\text{V}$ ,  $L = 2\text{mH}$ .

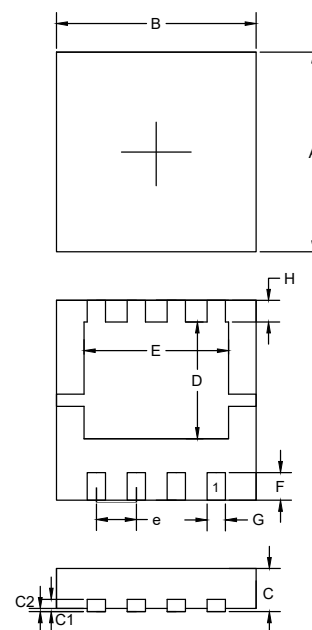
## Internal Structure and Marking Code



pin1

# N-CHANNEL MOSFET

## DFN3333



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.126	0.130	3.20	3.30	
B	0.126	0.130	3.20	3.30	
C	0.030	0.033	0.75	0.85	
C1	0.007	0.009	0.18	0.22	
C2	---	0.002	---	0.05	
D	0.071	0.079	1.80	2.00	
E	0.087	0.098	2.20	2.50	
F	0.016	0.020	0.40	0.50	
G	0.010	0.014	0.25	0.35	
H	0.012	0.016	0.30	0.40	
e	0.024	0.028	0.60	0.70	

**Electrical Characteristics @ 25°C (Unless Otherwise Specified)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	40			V
Gate-Source Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 10V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=20V, V_{GS}=0V$			1	$\mu A$
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.5	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$		3.3	4	m $\Omega$
		$V_{GS}=4.5V, I_D=15A$		4.4	5.2	m $\Omega$
Gate Resistance	$R_g$	F=1 MHz, Open drain		3.2		$\Omega$
<b>Diode Characteristics</b>						
Continuous Body Diode Current	$I_S$				50	A
Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=20A$		0.8	1.2	V
Reverse Recovery Time	$t_{rr}$	$I_F=20A, dI_F/dt=100A/\mu s$		22.3		ns
Reverse Recovery Charge	$Q_{rr}$			7.4		nC
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=20V, V_{GS}=0V, f=1MHz$		4645		pF
Output Capacitance	$C_{oss}$			436		
Reverse Transfer Capacitance	$C_{rss}$			360		
Total Gate Charge	$Q_g$	$V_{DS}=10V, V_{GS}=20V, I_D=20A$		102		nC
Gate-Source Charge	$Q_{gs}$			15.8		
Gate-Drain Charge	$Q_{gd}$			21.9		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=20V, V_{GS}=10V, R_{GEN}=3\Omega, I_D=20A$		12		ns
Turn-On Rise Time	$t_r$			54		
Turn-Off Delay Time	$t_{d(off)}$			120		
Turn-Off Fall Time	$t_f$			80		

**Curve Characteristics**

Fig. 1 - Typical Output Characteristics

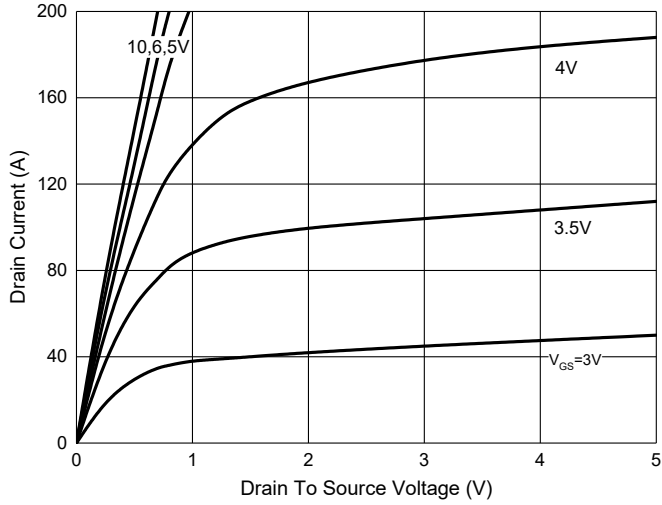


Fig. 2 - Transfer Characteristics

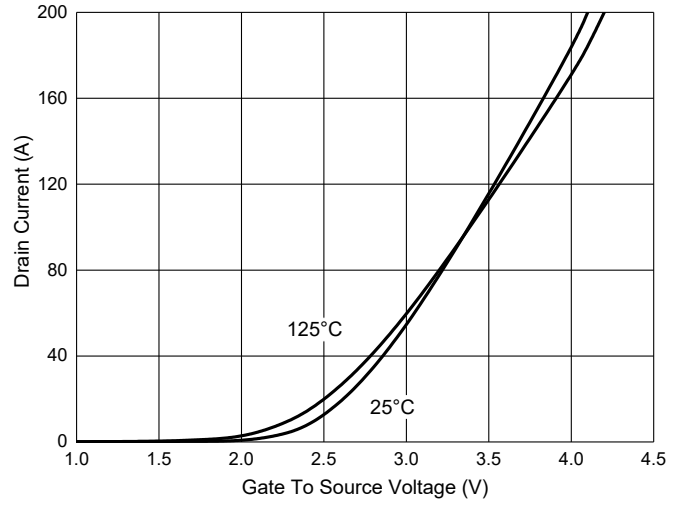


Fig. 3 -  $R_{DS(ON)} - I_D$

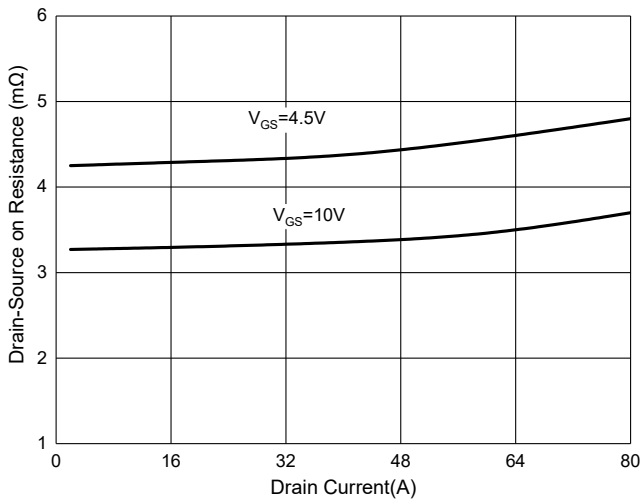


Fig. 4 - Normalized On Resistance Characteristics

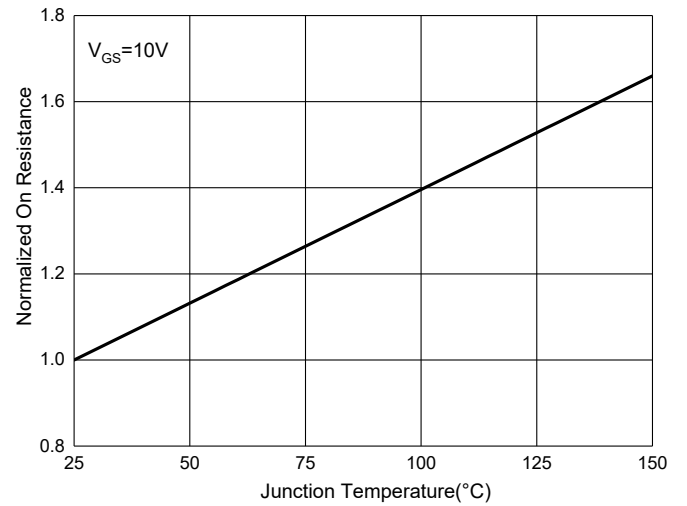


Fig. 5 - Capacitance Characteristics

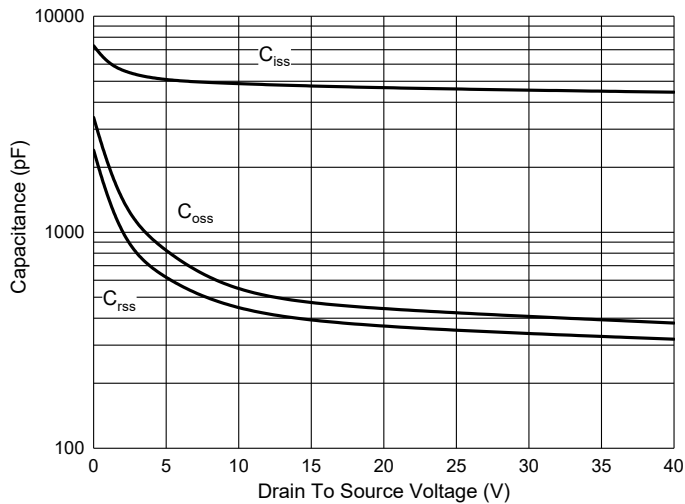
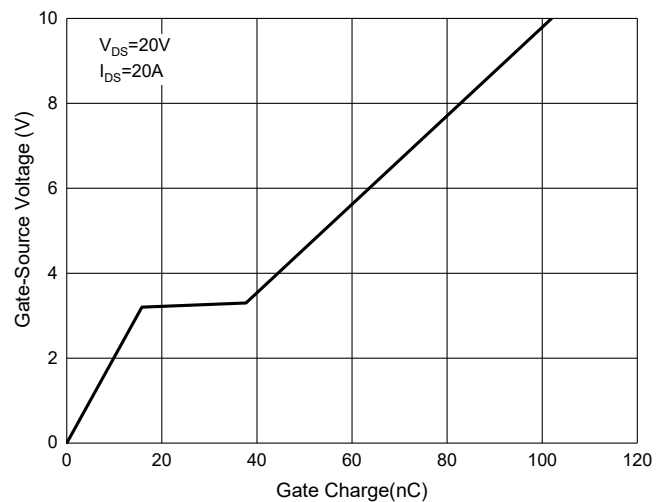


Fig. 6 - Gate Charge



**Curve Characteristics**

Fig. 7 - Safe Operation Area

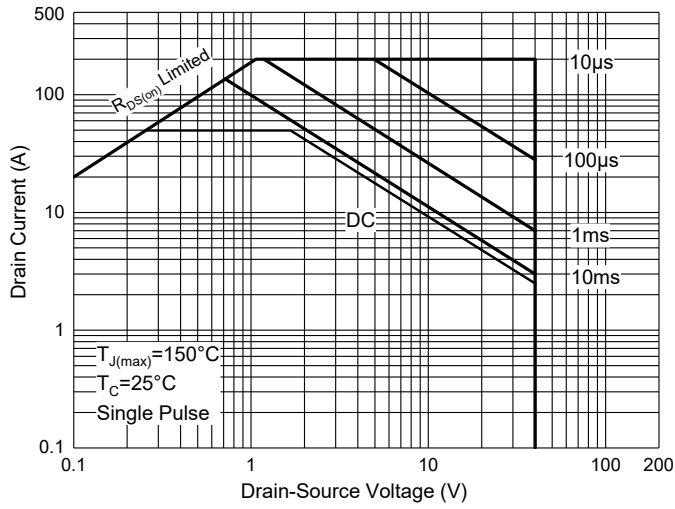
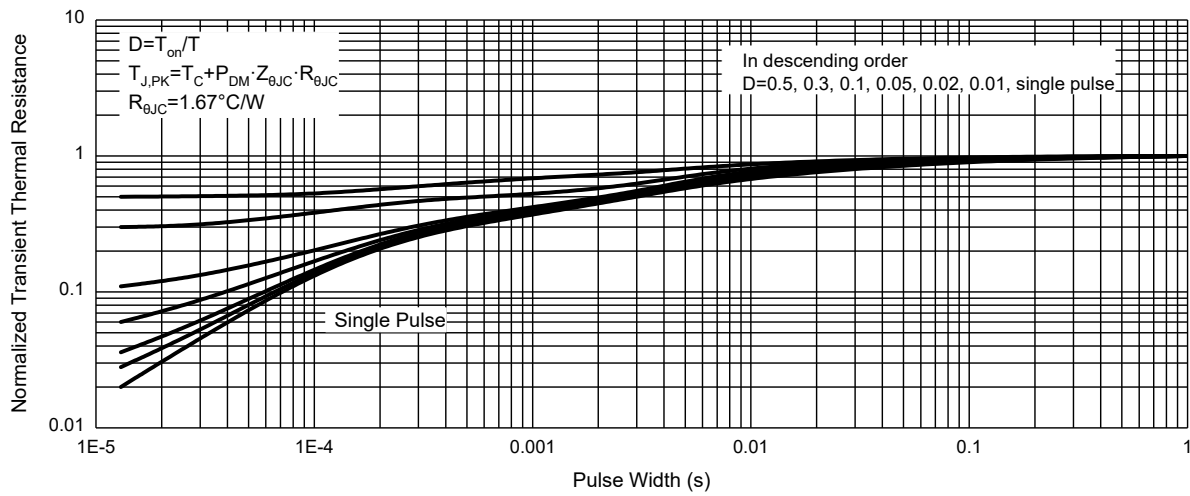


Fig. 8 - Normalized Transient Thermal Impedance



## Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 5Kpcs/Reel

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